

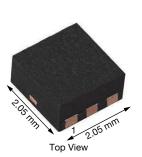
www.vishay.com

Vishay Siliconix

P-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (Typ.)						
-150	2.6 at V _{GS} = -10 V	-1.6 ^a	4.2 nC						
	2.7 at V _{GS} = -6 V	-1.6 ^a	4.2 110						

PowerPAK® SC-70-6L Single





Marking Code: B4
Ordering Information:

SiA485DJ-T1-GE3 (Lead (Pb)-free and halogen-free)

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Low on-resistance
- 100 % R_a and UIS tested

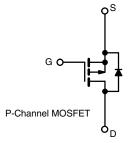
 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Active clamp switch
- · Load switch



ABSOLUTE MAXIMUM RATINGS	$\Gamma_A = 25 ^{\circ}\text{C}$, unless	otherwise note	ed)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	-150	V
Gate-Source Voltage		V _{GS}	± 20	¬
	T _C = 25 °C		-1.6	
Continuous Drain Current (T. – 150 °C)	T _C = 70 °C	Ι , Γ	-1.3	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	l _D	-0.7 b, c	
	T _A = 70 °C	1 [-0.57 ^{b, c}	
Pulsed Drain Current (t = 100 μs)	•	I _{DM}	-2	A
Cantinuous Sauras Drain Diada Current	T _C = 25 °C		-1.6	
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S	-1.6 ^{b, c}	
Avalanche Current	L = 0.1 mH	I _{AS}	-1.5	
Single Pulse Avalanche Energy	L = U.T IIII	E _{AS}	0.1	mJ
	T _C = 25 °C		15.6	
Maximum Dawar Dissipation	T _C = 70 °C]	10	w
Maximum Power Dissipation	T _A = 25 °C	P _D	2.9 b, c	VV
	T _A = 70 °C	1	1.8 ^{b, c}	
Operating Junction and Storage Temperature Ra	inge	T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature	d, e		260	

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum Junction-to-Ambient b, f	t ≤ 5 s	R _{thJA}	32	43	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	6	8	C/VV				

Notes

- a. $T_C = 25$ °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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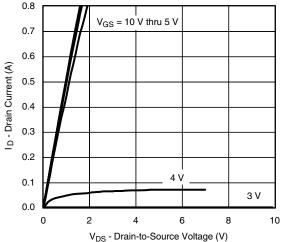
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = -250 \mu A$	-150	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-2.5	-2.5 -	-4.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zara Cata Voltaga Brain Current		V _{DS} = -150 V, V _{GS} = 0 V	-	-	-1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -150 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	-0.8	-	-	Α	
Dunin Course On Chata Desintance 3	0	V _{GS} = -10 V, I _D = -0.5 A	-	2.1	2.6	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -6 V, I _D = -0.5 A	-	2.2	2.7		
Forward Transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	-	1.5	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	155	-	pF	
Output Capacitance	C _{oss}	$V_{DS} = -75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	8	-		
Reverse Transfer Capacitance	C _{rss}		-	5.5	-		
Total Gate Charge	Qg		-	4.2	6.3	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -75 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	-	0.9	-		
Gate-Drain Charge	Q_{gd}		-	1.3	-		
Gate Resistance	Rg	f = 1 MHz	2	10	20	Ω	
Turn-On Delay Time	t _{d(on)}		-	5	10	ns	
Rise Time	t _r	V_{DD} = -75 V, R_L = 75 Ω	-	20	40		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	10	20		
Fall Time	t _f		-	20	40		
Drain-Source Body Diode Characteristi	cs						
Continuous Source-Drain Diode Current	IS	T _C = 25 °C	-		-1.6	^	
Pulse Diode Forward Current	I _{SM}		-		-2	A	
Body Diode Voltage	V _{SD}	$I_S = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.8	-1.2	V	
Body Diode Reverse Recovery Time	t _{rr}		-	40	80	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	-	65	130	nC	
Reverse Recovery Fall Time	t _a	$I_F = -1 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 ^{\circ}\text{C}$	-	28	-		
Reverse Recovery Rise Time	t _b		-	12	-	ns	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

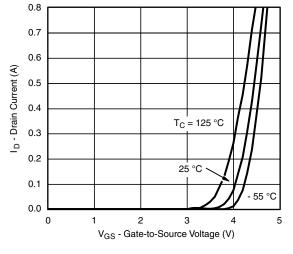
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



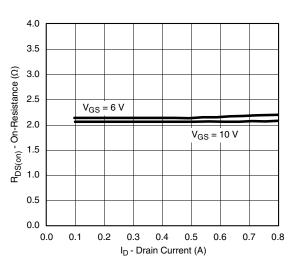


Output Characteristics

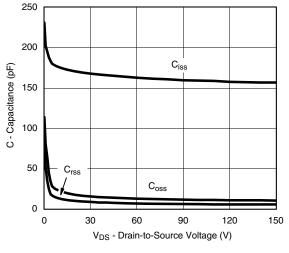
burce voltage (v)



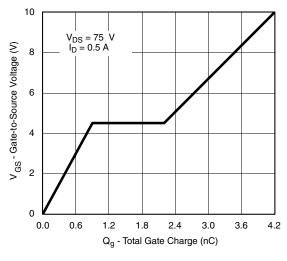
Transfer Characteristics



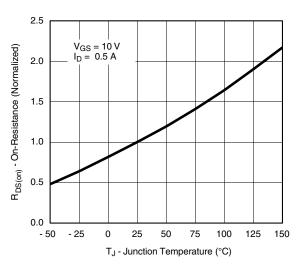
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

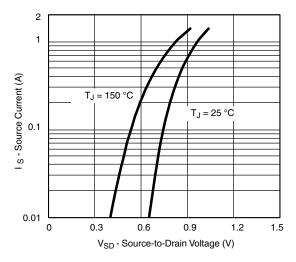




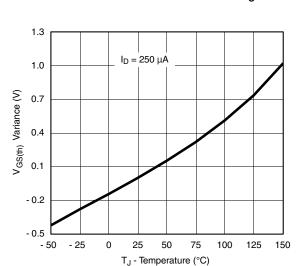


On-Resistance vs. Junction Temperature

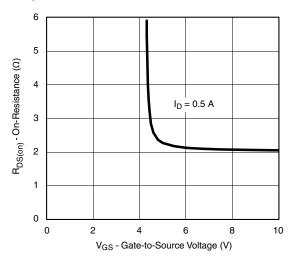




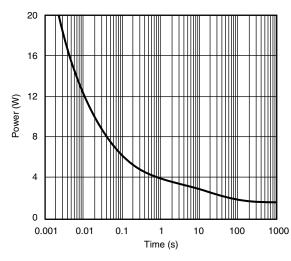
Source-Drain Diode Forward Voltage



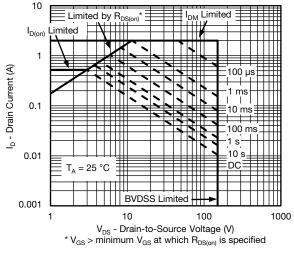
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

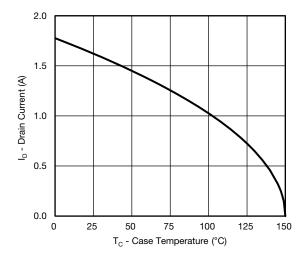


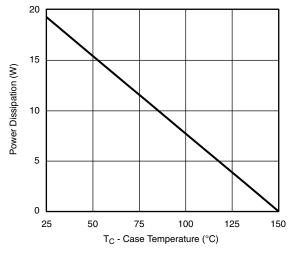
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient





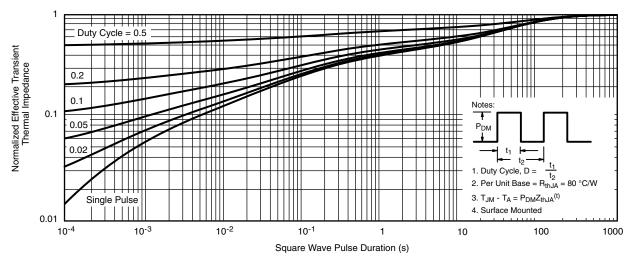


Current Derating*

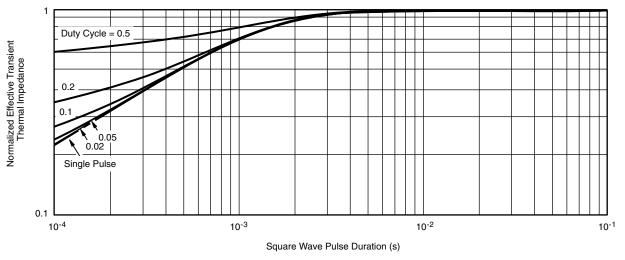
Power Derating

^{*} The power dissipation P_D is based on $T_{J \text{ (max.)}} = 150 \,^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

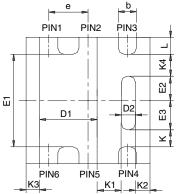
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62988.

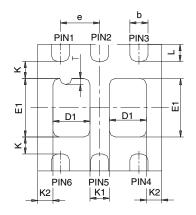




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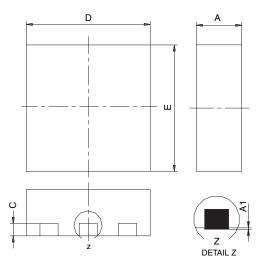
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	M	ILLIMETER	RS		INCHES		М	ILLIMETER	RS		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP	1	0.275 TYP		0.011 TYP			
K1		0.400 TYP			0.016 TYP		0.320 TYP		0.013 TYP			
K2		0.240 TYP		0.009 TYP		0.252 TYP		0.010 TYP				
К3		0.225 TYP		0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C O	C 07421 Pay C 06 Aug 07											

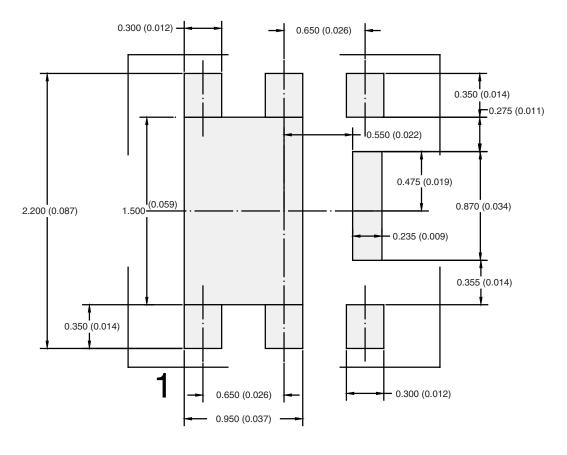
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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